Two-Electron Photon Emission from Metallic Quantum Wells

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U nusual em ission of visible light is observed in scanning tunneling m icroscopy of the quantum well system N a on Cu (111). Photons are em itted at energies exceeding the energy of the tunneling electrons. M odel calculations of two-electron processes which lead to quantum well transitions reproduce the experimental uorescence spectra, the quantum yield, and the power-law variation of the intensity with the excitation current.

PACS num bers: 73.20 At, 68.37 Ef, 73.20 M f, 73.21 Fg

Tunneling electrons in a scanning tunneling m icroscope (STM) can excite vibrational or electronic modes of the sam ple by inelastic tunneling provided that their energy exceeds the excitation energy. These excitations have been detected either by their contribution to the tunneling current [1] or by investigating light that is being em itted from the tunneling gap [2, 3]. Thus, inelastic tunneling spectroscopies have been perform ed. U sually, tunneling electrons can safely be assumed to be independent of each other in these spectroscopies. Even at a high tunneling current I = 100 nA the average time between two consecutive tunneling events is 1:6 ps. A ssum ing Poisson statistics, two electrons are rather unlikely to interact in the tunneling gap. As a consequence, inelastic processes which involvem ultiple electrons have only been observed in the particular case of STM -induced desorption of H from Si. The lifetime of the H-Sistretch mode which is involved in desorption is in the range of nanoseconds [4] enabling an interaction with several consecutive electrons before deexcitation.

Here, we report on unusual emission of visible light from Na on Cu(111), a metallic system which exhibits well-studied quantum well states (QWS) near the Ferm i energy E_F [5, 6, 7, 8, 9, 10, 11, 12]. Surprisingly, uorescence spectra reveal the emission of \forbidden" photons whose energy h signi cantly exceeds the energy of a tunneling electron eU, where U is the sam ple voltage. The intensity of the \forbidden" light increases approximately like I^{1:5} where I is the tunneling current, with the exponent decreasing to 12 at the highest currents used. Its quantum e ciency reaches values of up to 10⁻⁷ photons per tunneling electron at large I.

E lectronic lifetim es at the Na/Cu (111) surface being on a fs tim escale [10] we are lead to conclude that twoelectron processes are involved which do not rely on a stepw ise accum ulation of energy in an excited mode. W e propose a model where two electrons tunnelmore or less sim ultaneously. Once they are in the vacuum -barrier region between tip and sample they may exchange energy through the C oulom b interaction which is relatively unscreened there. As a result of this A uger-like process, one of the electrons can emit a photon with h > eU. Despite the simplicity of the model, calculated uorescence spectra and the current dependence of the quantum eciencies are comparable to the experimental data.

Spectral structure extending beyond the condition h < eU has been reported for photon emission from Au Im s investigated at ambient temperature. However, no explanation of this intriguing result is currently available [13]. U chara et al. [14] reported on light emission at h = 2 eU from superconducting Nb tips and samples at T = 4.7 K and explained this emission in terms of C cooper-pair tunneling. P hoton emission at large h has also be observed from m etal point contacts which emit black-body radiation at elevated currents [15].

Our experiments were performed with a ultra-high vacuum (UHV) STM operated at a tem perature T = 4:6 K[16]. W tips were prepared by electrochem ical etching and subsequent sputtering and annealing in UHV. The Cu (111) surface was cleaned by repeated cycles of Ar-ion bom bardm ent and annealing. Na Im swere evaporated from outgassed SAESG etters sources onto the Cu crystal held at room tem perature. Na coverages were calibrated using the binding energies of the lowest QW S [10]. A fter preparation at room tem perature the sam ples were transferred to the STM and cooled to T = 4.6 K. Photons in the energy range 1.1 eV < h < 3.5 eV were detected with a lens-system in UHV, coupling the light to a grating spectrom eter and a liquid nitrogen cooled CCD cam era [17]. The spectra have been corrected for the wavelength dependency of the detection e ciency. For the voltages used here, up to currents of 100 nA, surface m odi cations was rarely observed on at surfaces. W hile surface m odi cation becom es m ore probable at higher currents, during acquisition of the data sets shown here no such events occured as ver ed from STM im ages and simultaneous monitoring of the vertical tip position.

Figure 1 displays uorescence spectra recorded at el-

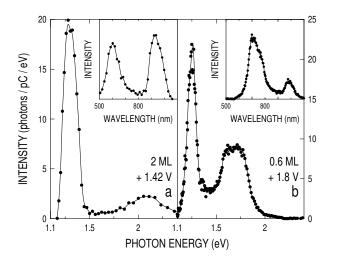


FIG.1: Fluorescence spectra from N a m onolayers on Cu (111). (a) 2 M L N a, U = 1:42 V, I = 100 nA. (b) 0.6 M L N a, U = 1:80 V, I = 357 nA. Solid lines serve to guide the eye. The data have been corrected for detector response. How ever, due uncertainties of the rapidly decreasing detector sensitivity at photon energies below 1:25 eV the correction is reliable only at higher photon energies. The insets show the uncorrected data as m easured (in counts vs. wavelength in nm)

evated tunneling currents from a (a) 2 M L and (b) 0.6 MLNa lm on Cu (111). The QW S binding energies are known from tunneling spectroscopy [18]. At 2 M L, unoccupied states exist at $E_1 = 0.15 \text{ eV}$ and $E_2 = 2.2 \text{ eV}$. At 0.6 M L, these states are located at $E_1 = 0.4$ eV and $E_2 = 2:1 \text{ eV}$. Previously, photon em ission due to two processes has been reported from these layers [3, 19]. At low U, i.e. $eU < E_2$, electrons tunnel inelastically from the tip Ferm i level to the low er QW S and em it photons. Fluorescence spectra revealam axim um which shifts with eU. When $eU > E_2$, tunneling to the upper QWS occurs and a subsequent transfer of an electron to the lower QWS gives rise to the emission of quantum well lum inescence at $h = E_2 = E_1 \cdot E_1$ a hancement by a local plasm on renders these processes e cient. The data of Fig. 1 appears to be consistent with this picture. Two spectral components are discernible, an emission at low photon energies involving inelastic tunneling and an additional peak at (a) h 2:0 eV and (b) h 1:7 eV which is due to transitions between QW S.W hat is new in Fig. 1 is the fact that these data were recorded at a sam ple voltage (a) U = 1:42 V and (b) U = 1:80 V. In Fig. 1a the entire quantum well emission peak seems to violate energy conservation, h 2 eV > eV with a maximum energy excess of 0:7 eV. In Fig. 1b there is still signi cant intensity with h > eU. However, the quantum well 1:7 eV in Fig. 1b becom es even more em ission at h surprising if one recalls that the upper QW S, which is involved in the underlying transition, is located at $E_2 = 2:1$ eV which is substantially larger than eU.

Two-electron processes provide a natural explanation

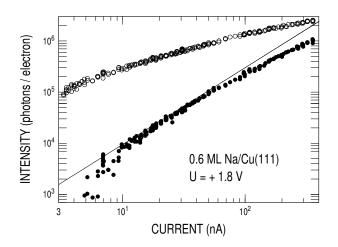


FIG.2: Intensity of quantum well emission (dots, 1.45 eV < h < 2 eV, connected for detection e ciency) and emission due to inelastic tunneling (circles, 1.1 eV < h < 1.45 eV) vs.current I evaluated from 830 uorescence spectra of a 0.6 M L coverage at U = 1.8 V. As a guide to the eye a slope of $I^{1:5}$ is indicated (line).

of the unusual emission in Fig. 1. Since such processes im ply a nonlinear variation of the intensity with the tunneling current I we recorded series of som e 800 uorescence spectra while varying I and evaluated the \forbidden" intensity. The double-logarithm ic plot in Fig. 2 reveals that the intensity scales approximately like I^{1:5} con ming the above explanation. As a consequence, the \forbidden" em ission is weak at low tunneling currents. That is why it has been overlooked previously. In addition to its variation with I, the intensity of the quantum well emission from 0.6 M L Na also depends strongly on the voltage U for U < 2 V. Consequently, the quantum e ciency of the \forbidden" em ission varies signi cantly depending on the specic I and U chosen. W e estimate an e ciency on the order of 10^{-7} photons per tunneling electron at I = 100 nA and U = 1.8 V from 0.6 M L Na.

A possible explanation of the observed two-electron processes appears to be tunneling of an electron into a long-lived empty state of the Na/Cu(111) surface and subsequent further excitation of this electron via interaction with a second tunneling electron. We estimated the probability of such processes assuming a Poisson distribution of the intervals between tunneling events. To obtain the observed quantum e ciencies an excited electronic state with a lifetime 1 ps needs to be postulated. This value is much larger than typical electronic lifetim es at surfaces. Moreover, it is unclear why an electron should remain localized under the tip over this extended period of time. We therefore discard this type of mechanism.

We have instead considered two other two-electron mechanisms that we believe cause emission of photons with an energy exceeding eU: (i) A coherent Auger-like process in which energy is transferred from one tunneling electron to another. (ii) Decay of the hot holes [20] that are injected into the tip because most of the tunneling current passes through the low erQW S.The decaying holes create hot electrons in the tip which subsequently can tunnel into the upper QW S and thereby cause photon em ission.

The Keldysh G reen's function (GF) formalism provides a suitable theoretical fram ework for calculating the intensity of the em itted light from a system out of equilibrium such as an STM under nite bias. The intensity can be written [19]

$$\frac{dP}{d d(h!)} = \frac{!^2 j (!)^2}{16^{3} c^{3} h} \int_{V}^{Z} d^3 r d^3 r^0 i^{<} (r; r^0; !): (1)$$

The integrations run over a volum e between the tip and sample where the electrons and photons interact e ciently. G is a factor describing the enhancem ent of the electrom agnetic vacuum uctuations in the tip-sample cavity, and < is the Fourier transform of the currentcurrent GF, $ihj_{z}(\mathbf{r}^{0};0)j_{z}(\mathbf{r};t)i$, which in the case of allowed light em ission can be expressed in term s of a current matrix element between the initial and nale lectron states [19]. The detailed calculations of electron states and matrix elements employs a one-dimensional model for the system . The C u potential is corrugated to yield a band gap of 5 eV at the Brillouin zone boundary, while the potential in the N a layer and the tip are assumed to be constant [21]. A tilted square barrier, rounded and low ered by in age-potential contributions, separates the electrodes. In addition, the potential in the Na layer is given an imaginary part i, with = 0.1 eV, to m im ic the electron scattering processes that lim it the lifetime of the quantum well states.

For forbidden light em ission through an Auger-like process, the leading contribution to the integrals in Eq. (1) can be written in term s of a sum of the squares of secondorder m atrix elem ents,

$$\frac{dP}{d \ d(h!)} = \frac{!^{2} \mathbf{j} \mathbf{G} (!) \mathbf{j}^{2}}{8 \ ^{2} \ _{0} c^{3}} \mathbf{M}_{k_{1} k_{2} q} \mathbf{M}_{k_{1} ; k_{2} ; q} \mathbf{j}^{2}$$

$$(\mathbf{E}_{k_{1}} + \mathbf{E}_{k_{2}} \mathbf{E}_{1 ; k_{1} + q} \mathbf{E}_{1 ; k_{2} q} \mathbf{h}!): (2)$$

M $_{k_1,k_2,q}$ describes how two electrons in the tip labeled by the momenta K_1 and K_2 rst interact through a screened C oulom b interaction, $e^2e^{-jr_1-r_2}j=(4_0jr_1-r_2j)$ and exchange energy and momentum [22]. One electron goes into the lower QWS [with in-plane momentum $k_{1,k}^2 + q$ and energy $E_{1,k_1+q} = E_1 + h^2 (k_{1,k}^2 + q)^2 = (2m)$] directly and takes no further part in the process, while the other eventually emits a photon in a transition from an interm ediate state into the lower QWS (with in-planem om entum $k_{2,k}^2$ q and energy E_{1,k_2-q}). When the two electrons have opposite spin we can write

$$M_{k_1;k_2;q} = \frac{ieh}{2m} \int_{V}^{Z} \int_{V}^{$$

$$\frac{e^{2}}{e^{2}} (\mathbf{r}) \frac{e^{2}}{e^{2}} (\mathbf{r}; \mathbf{r}_{2}) \frac{e^{2}}{e^{2}} \frac{e^{-j\mathbf{r}_{1}} \mathbf{r}_{2}}{e^{2}} \frac{e^{-j\mathbf{r}_{1}} \mathbf{r}_{2}}{e^{2}} g^{r} (\mathbf{r}; \mathbf{r}_{2})$$

$$\frac{e^{2}}{4} \frac{e^{-j\mathbf{r}_{1}} \mathbf{r}_{2}}{e^{j\mathbf{r}_{1}} \mathbf{r}_{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{1}} \mathbf{r}_{2}}{e^{2}} (\mathbf{r}_{2}) \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{1}} \mathbf{r}_{2}}{e^{2}} (\mathbf{r}_{2}) \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} (\mathbf{r}_{2}) \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} \frac{e^{2}}{e^{2}} e^{-j\mathbf{r}_{2}} \frac{e^{2}}{e^{2}} \frac{e^{2}}{e^{$$

where denotes the QWS wave function, while stands for tip wave functions. The retarded electron G reen's function g^r describes the propagation of the electron in the intermediate state before photon emission. For energy and momentum conservation to hold in the photon emission process the energy and in-plane momentum in the intermediate state must be $E_{1;k_2 q} + h!$ and $k_{2;k}^{\sim}$ q, respectively. The electron G reen's function has a resonance when its energy argument coincides with the energy of the upper QWS which explains why, as we will see, the forbidden light emission mainly produces photons with energy h = $E_2 = E_1$.

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We have also calculated the light emission intensity as a result of hot-hole decay. To this end we studied a semiclassicalm odelbased on Ref.23 for hot-hole-electron cascade and di usion (with an elastic mean free path of 2 nm) in the tip, and calculated the in ux of secondary hot electrons onto the tip apex. This in ux was then used as input in a calculation of the light emission intensity along the line of Ref. 19.

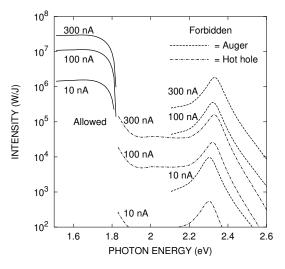


FIG.3: \A llowed" and \forbidden" light em ission calculated for a m odel system with QW S at $E_1 = 0.2$ eV and $E_2 = 2.5$ eV. R esults are shown for various currents indicated in the gure and a voltage U = 2 V. The thickness of the N a overlayer was set to 0.613 nm, corresponding to 2 m onolayers.

Figure 3 displays results from our model calculations obtained for U = 2 V and I = 10, 100, and 300 nA, respectively. The model potential leads to $E_1 = 0.2 \text{ eV}$ and $E_2 = 2.5 \text{ eV}$ at U = 2 V. Under these conditions, the upper quantum well state at E_2 is not accessible. Moreover, the energy eU of a single electron is not su cient for exciting the corresponding quantum well transition. As a result, one-electron processes (solid lines in Fig. 3) give rise to plasm on mediated em ission by inelastic tunneling from the tip Ferm i level only to the lower QW S. The em ission occurs predom inantly at $h < eU = E_1$ as expected [3, 19].

The emission calculated for the Auger-like and hot-hole processes, respectively, are indicated by dashed lines. We do nd sizable emission, which is about one order of magnitude stronger for the Auger process than the hot-hole mechanism, peaked at h 2:3 eV (thus h > eU) due to quantum well transitions. The electron that eventually causes the light emission gains enough energy (i.e.

0.5 eV), either through C oulom b interactions with another electron while tunneling, or in the hot-hole-electron cascade in the tip, to be promoted to the upper quantum well resonance situated above the tip Ferm i level in energy. We note that the particular electronic structure of N a on C u (111) with states at well-de ned energies is essential in achieving signi cant signal levels.

The calculations predict quantum yields of up to 10⁻⁷ photons per electron for the Auger-like mechanism at I=100 nA and U=2.3 V in reasonable agreement with the experimental value. Given the experimental uncertainty of absolute photon intensities, as well as the approximations involved in the calculations, a comparison of its variation with I is more signi cant. The Auger-like process yields I^{1:5} close to the experimental data [24]. The hot-hole process gives a slightly larger exponent, 1.6. W hile both mechanism s must be considered as plausible explanations for the forbidden light emission the larger calculated intensities indicate that the Auger process is the dom inating one.

In summary, we reported on unusual STM -induced photon emission from a metallic quantum well system at photon energies exceeding the limit h eU. Model calculations revealed that owing to the particular electronic structure of N a on Cu (111) two-electron processes can cause quantum well transitions and corresponding uorescence. Similar elects may be observable in other quantum con ned system s.

W e acknowledge support by the European Commission (IMR EMIT), the Deutsche Forschungsgemeinschaft and the Swedish Research Council (VR).

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- [24] This value deviates from the intuitive expectation of an exponent 2 for two-electron processes. A more detailed analysis reveals that the exponent is a ected by the effective thickness of the tunneling barrier that an electron has to overcom e. This thickness decreases for increasing energy of the tunneling electrons. C onsequently, a change of the tip-sam ple distance leading to a given increase of the total tunneling current is com prised of a weaker current increase of high energy electrons and a larger increase at low energies. As a result, the calculated exponent 1.5 for two-electron processes, i.e. electrons at high energies, is smaller than 2. (This last note was om itted from the published paper for lack of space.)